# Method of forming a Static Random Access Memory with a Buried Local Interconnect

ABSTRACT OF THE DISCLOSURE

An SRAM cell includes six transistors. The storage nodes are implemented using local interconnects. A first level of metal overlies the interconnects but is electrically isolated therefrom. Contact plugs are formed to couple the cell to the first level of metal. The contact plugs are preferably formed in a different process step than the interconnects.

Figure 4a